

A method for fabricating a nitride read-only memory is described. An ONO stacked layer and a protective layer are sequentially formed on a substrate. A patterning/etching process is performed to pattern the protective layer and the ONO stacked layer to expose a portion of the substrate. Thereafter, the protective layer is removed by using wet etching. An ion implantation is performed to form buried bit lines in the exposed substrate, and then an insulator is formed on each buried bit line. A plurality of word lines are formed on the substrate crossing over the buried bit lines.

## Figures